Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A gap fill material forming composition ~~wherein the composition is used in manufacture of~~ for manufacturing semiconductor ~~device~~ devices by ~~a method comprising~~ coating a photoresist on a substrate having a hole with an aspect ratio of 1 or more shown in ~~height/diameter of 1 or more,~~ height/diameter, ~~and~~ transferring an image to the substrate ~~by use of~~ using a lithography process, coating the composition ~~is used in a process in which the composition is coated~~ on the substrate, baking the composition, ~~is contacted~~ contacting the composition with an alkaline aqueous solution after baking, ~~then~~ and coating the ~~photoresist is coated,~~ photoresist, the composition ~~comprises~~ comprising:

a polymer having a hydroxy group or a carboxy ~~group~~ group; ~~and~~

a crosslinking ~~agent,~~ agent; and

an alkali-dissolution rate regulator selected from the group consisting of naphthoquinone compounds, compounds having a t-butoxycarbonyl group, compounds having a hydroxy group, compounds having a carboxy group, and compounds having a phenyl group, ~~and~~

wherein a gap fill material layer manufactured by coating and baking the gap fill material forming composition on a semiconductor substrate ~~and baking it~~ has a dissolution rate ~~for an alkaline aqueous solution having a concentration of 0.1% to 20%~~ ranging from 3 to 200 nm per ~~second.~~ second for an alkaline aqueous solution having a concentration of 0.1% to 20%.

2. (Original) The gap fill material forming composition according to claim 1, wherein the polymer has a weight average molecular weight of 500 to 30000.

3. (Original) The gap fill material forming composition according to claim 1, wherein the polymer is a polymer containing repeating unit having a hydroxy group or a carboxy group in main chain.

4. (Original) The gap fill material forming composition according to claim 1, wherein the polymer is a polymer containing repeating unit having a hydroxy group or a carboxy group in side chain.

5. (Original) The gap fill material forming composition according to claim 1, wherein the polymer is a polymer containing acrylic acid or methacrylic acid as repeating unit.

6. (Original) The gap fill material forming composition according to claim 1, wherein the polymer is a polymer containing hydroxyalkyl acrylate or hydroxyalkyl methacrylate as repeating unit.

7. (Original) The gap fill material forming composition according to claim 1, wherein the polymer is a dextrin ester compound.

8. (Original) The gap fill material forming composition according to claim 1, wherein the polymer is a polymer containing hydroxystyrene as repeating unit.

9. (Previously Presented) The gap fill material forming composition according to claim 1, wherein the polymer has no aromatic ring structure in the structure.

10. (Original) The gap fill material forming composition according to claim 1, wherein the crosslinking agent is a crosslinking agent having at least two crosslink-forming functional groups.

11. (Canceled)

12. (Previously Presented) A method for forming a gap fill material layer for use in manufacture of semiconductor device comprising coating the gap fill material forming composition according to claim 1 on a substrate and baking it.

13. (Canceled)